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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Not Yet Assigned
				Filing Date	July 9, 2003
				First Named Inventor	Won-Ho Lee
				Art Unit	Not Yet Assigned
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	29926/39502

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SA		Fujieda et al., "Dependence of Si PN Junction Perimeter Leakage on the Channel-Stop Boron Dose and Interlayer Material" (IEEE ELECTRON DEVICE LETTERS, VOL. 20, NO. 8, AUGUST 1999, Pages 418-420)	
SP		Morris et al., "An Accurate and Efficient Model for Boron Implants Through Thin Oxide Layers into Single-Crystal Silicon" (IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING, VOL. 8, NO. 4, NOVEMBER 1995, Pages 408-413)	
SP		Walter et al., "Dopant Channeling as a Function of Implant Angle for Low Energy Applications" (IEEE, 1999, Pages 126-129)	
SA		Son et al., "Blanket Tilt Implanted Shallow Trench Isolation (BTI-STI) Process for Enhanced DRAM Retention Time Characteristics" (IEEE, 1999, Pages 122-124)	

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Examiner Signature	<i>Shumney Shu</i>	Date Considered	3/16/04
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